

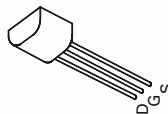
# N-CHANNEL ENHANCEMENT MODE VERTICAL DMOS FET

ISSUE 2 - MARCH 94

## FEATURES

- \* 350 Volt  $V_{DS}$
- \*  $R_{DS(on)}=50\Omega$

# ZVN0535A



E-Line  
TO92 Compatible

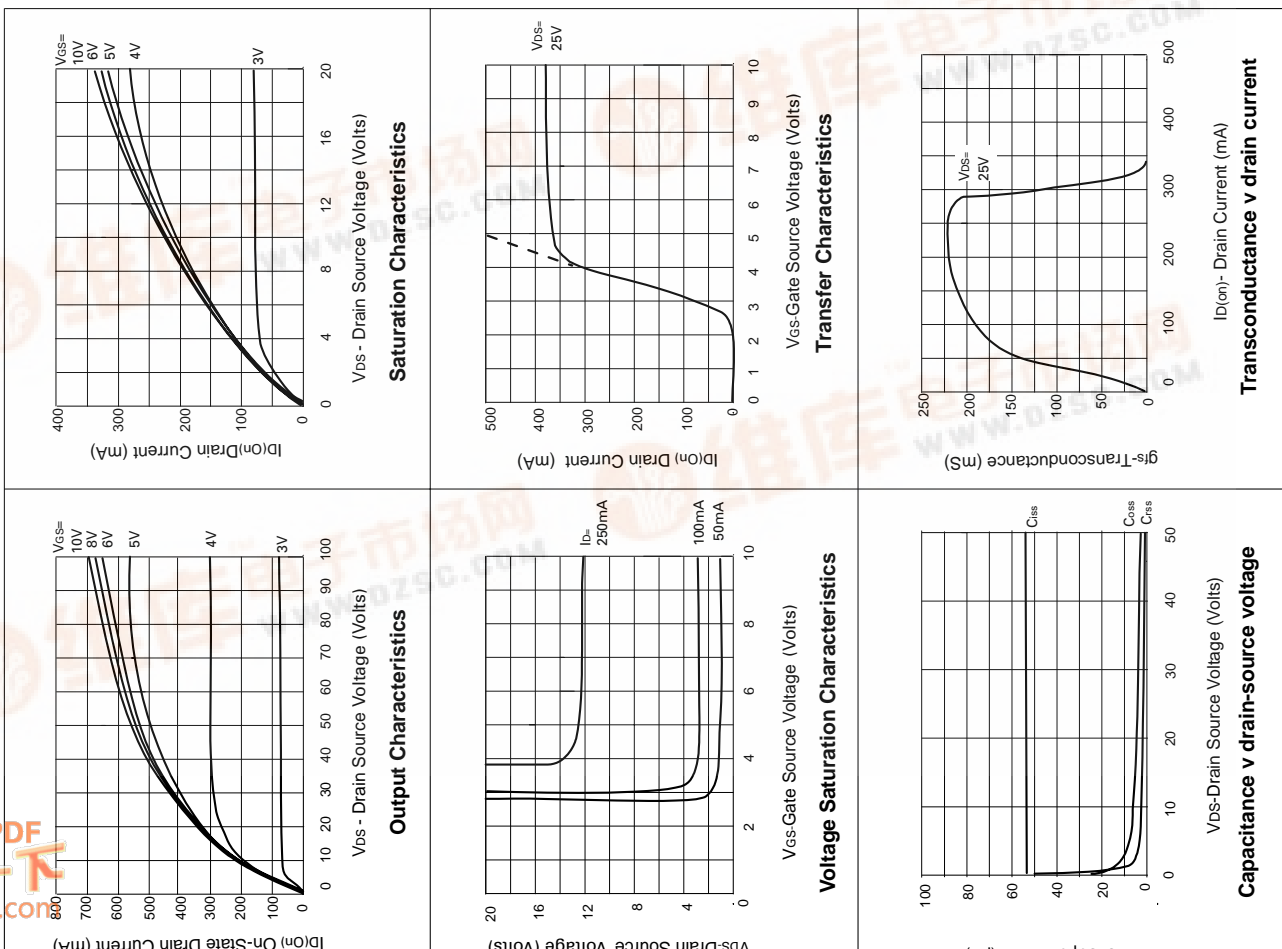
## ABSOLUTE MAXIMUM RATINGS.

PARAMETER	SYMBOL	VALUE	UNIT
Drain-Source Voltage	$V_{DS}$	350	V
Continuous Drain Current at $T_{amb}=25^{\circ}C$	$I_D$	90	mA
Pulsed Drain Current	$I_{DM}$	600	mA
Gate Source Voltage	$V_{GS}$	$\pm 20$	V
Power Dissipation at $T_{amb}=25^{\circ}C$	$P_{tot}$	700	mW
Operating and Storage Temperature Range	$T_j, T_{stg}$	-55 to +150	$^{\circ}C$

## ELECTRICAL CHARACTERISTICS (at $T_{amb} = 25^{\circ}C$ unless otherwise stated).

PARAMETER	SYMBOL	MIN.	MAX.	UNIT	CONDITIONS.
Drain-Source Breakdown Voltage	$BV_{DSS}$	350		V	$I_D=1mA, V_{GS}=0V$
Gate-Source Threshold Voltage	$V_{GS(th)}$	1	3	V	$I_D=1mA, V_{DS}=V_{GS}$
Gate-Body Leakage	$I_{GSS}$		20	nA	$V_{GS}=\pm 20V, V_{DS}=0V$
Zero Gate Voltage Drain Current	$I_{DSS}$		10 400	$\mu A$ $\mu A$	$V_{DS}=350V, V_{GS}=0V$ $V_{DS}=280V, V_{GS}=0V, T=125^{\circ}C(2)$
On-State Drain Current (1)	$I_{D(on)}$	150		mA	$V_{DS}=25V, V_{GS}=10V$
Static Drain-Source On-State Resistance (1)	$R_{DS(on)}$		50	$\Omega$	$V_{GS}=10V, I_D=100mA$
Forward Transconductance (1)(2)(3)	$g_{fs}$	100		mS	$V_{DS}=25V, I_D=100mA$
Input Capacitance (2)	$C_{iss}$		70	pF	
Common Source Output Capacitance (2)	$C_{oss}$		10	pF	$V_{DS}=25V, V_{GS}=0V, f=1MHz$
Reverse Transfer Capacitance (2)	$C_{rss}$		4	pF	
Turn-On Delay Time (2)(3)	$t_{d(on)}$		7	ns	
Rise Time (2)(3)	$t_r$		7	ns	$V_{DD}=25V, I_D=100mA$
Turn-Off Delay Time (2)(3)	$t_{d(off)}$		16	ns	
Fall Time (2)(3)	$t_f$		10	ns	

## TYPICAL CHARACTERISTICS



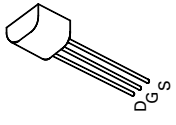
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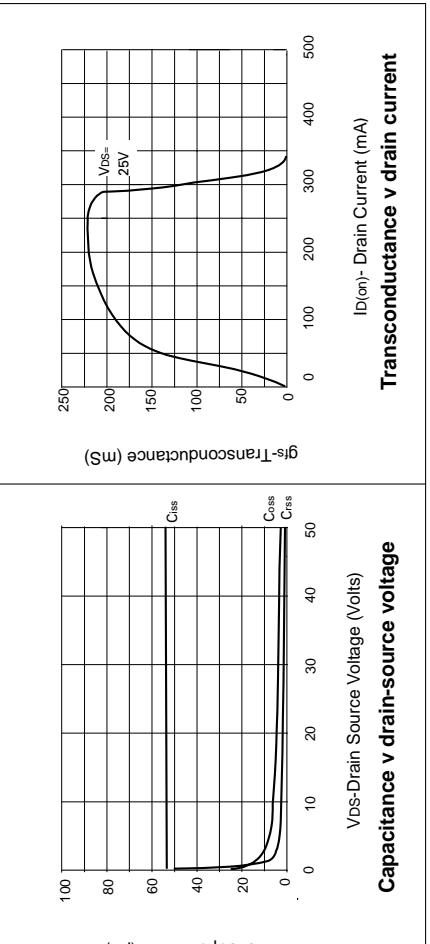
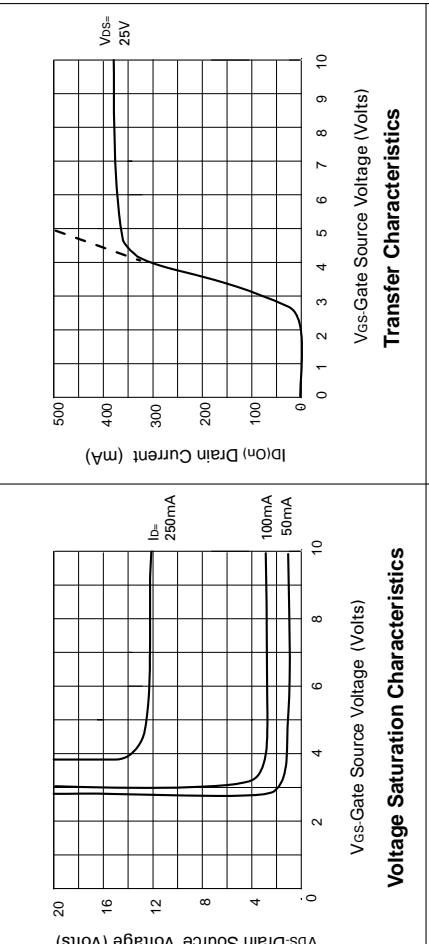
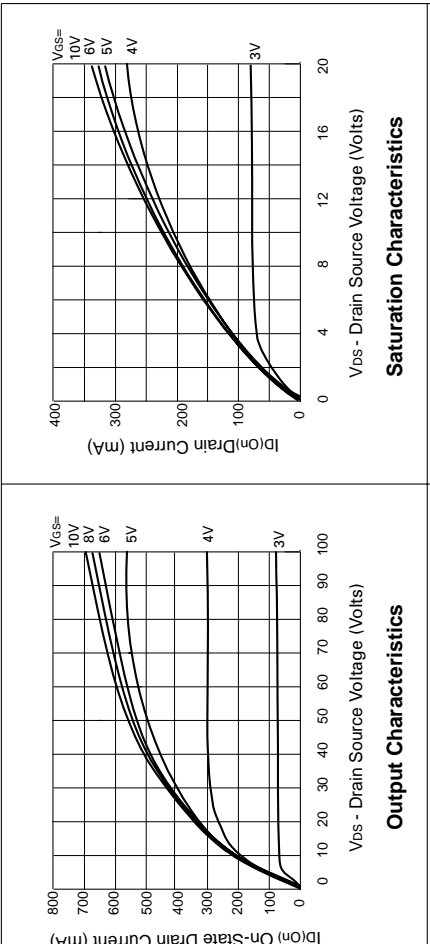
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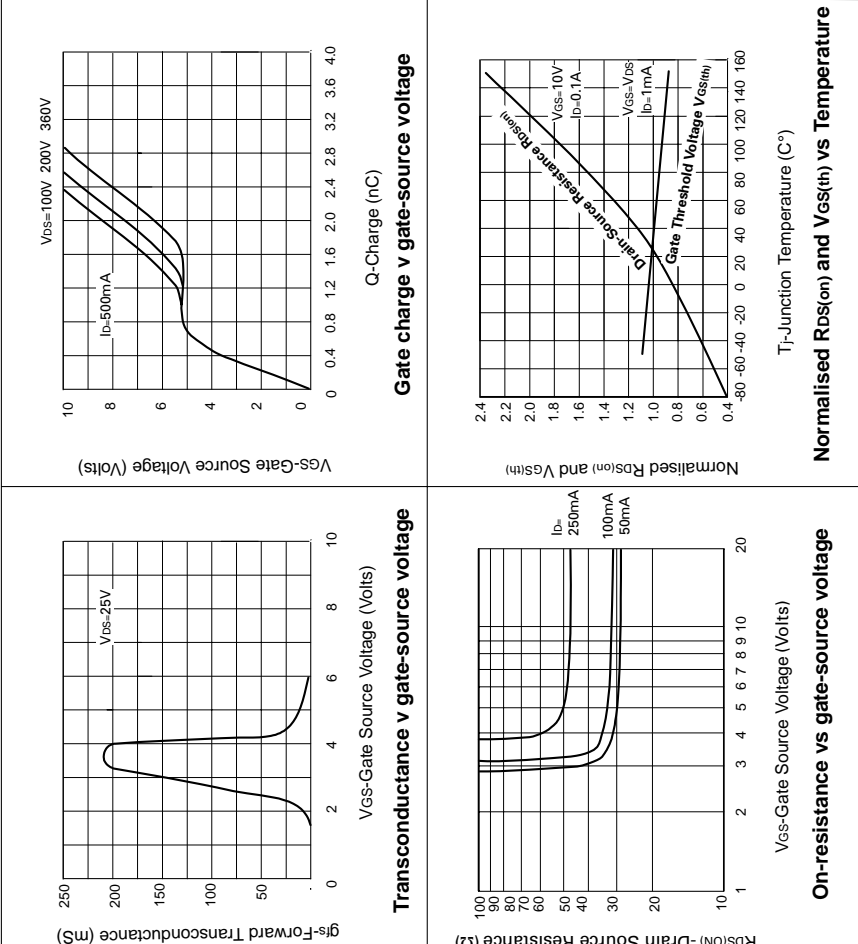
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## TYPICAL CHARACTERISTICS



Normalised R<sub>DS(on)</sub> and V<sub>GS(th)</sub> vs Temperature